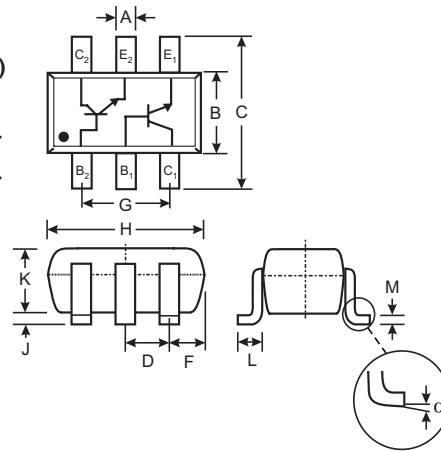


Features

- Epitaxial Planar Die Construction
- Intrinsically Matched NPN Pair (Note 1)
- Small Surface Mount Package
- 2% Matched Tolerance, h_{FE} , $V_{CE(SAT)}$, $V_{BE(SAT)}$
- Available in Lead Free/RoHS Compliant Version (Note 4)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 5, Below
- Terminal Connections: See Diagram
- Marking (See Page 2): K4A
- Marking Code & Date Code Information: See Page 2
- Ordering Information: See Below
- Weight: 0.015 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	8°	
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	DMMT3904W	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	200	mA
Power Dissipation (Note 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Ordering Information (Note 3)

Device	Packaging	Shipping
DMMT3904W-7	SOT-363	3000/Tape & Reel

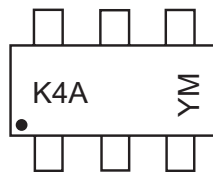
- Notes:
1. Built with adjacent die from a single wafer.
 2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 4. No purposefully added lead.
 5. For Lead Free/RoHS compliant version part number, please add "-F" suffix to the part number above. Example: DMMT3904W-7-F.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Base Cutoff Current	I_{BL}	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
ON CHARACTERISTICS (Note 6)					
DC Current Gain (Note 7)	h_{FE}	40 70 100 60 30	— — 300 — —	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage (Note 7)	$V_{CE(SAT)}$	—	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 7)	$V_{BE(SAT)}$	0.65 —	0.85 0.95	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Voltage Matching	ΔV_{BE}	—	1	mV	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.0	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	—	8.0	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1.0	10	k Ω	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.5	8	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	$V_{CE} = 20\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Noise Figure	NF	—	5.0	dB	$V_{CE} = 5.0\text{V}, I_C = 100\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA}, V_{BE(off)} = -0.5\text{V}, I_{B1} = 1.0\text{mA}$
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	200	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA}, I_{B1} = I_{B2} = 1.0\text{mA}$
Fall Time	t_f	—	50	ns	

- Notes: 6. Short duration test pulse used to minimize self-heating effect.
7. The DC current gain, h_{FE} , (matched at $I_C = 10\text{mA}$ and $V_{CE} = 1.0\text{V}$) Collector Emitter Saturation Voltage, $V_{CE(SAT)}$, and Base Emitter Saturation Voltage, $V_{BE(SAT)}$ are matched with typical matched tolerances of 1% and maximum of 2%.

Marking Information

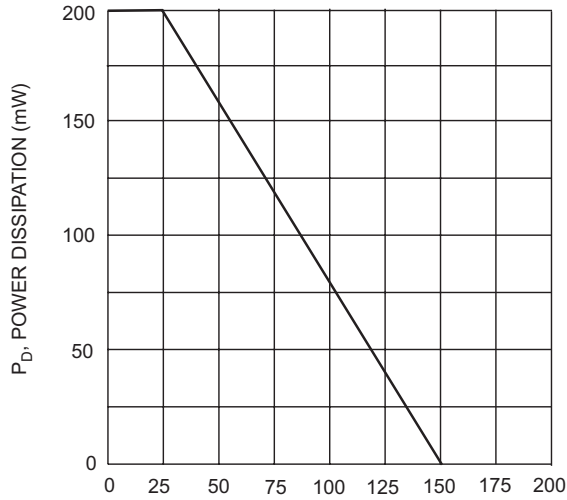


K4A = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

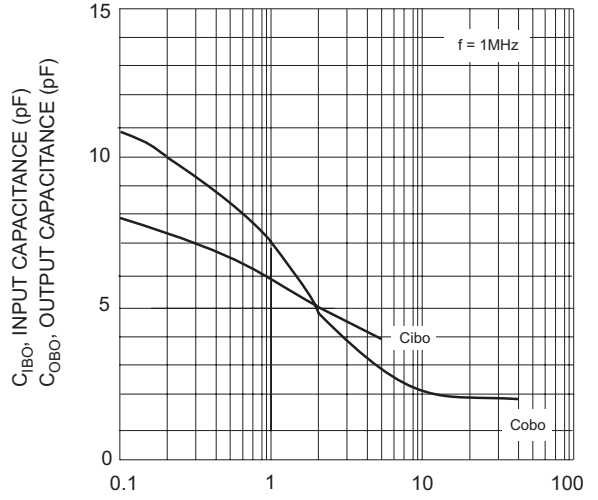
Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008
Code	N	P	R	S	T	U	V

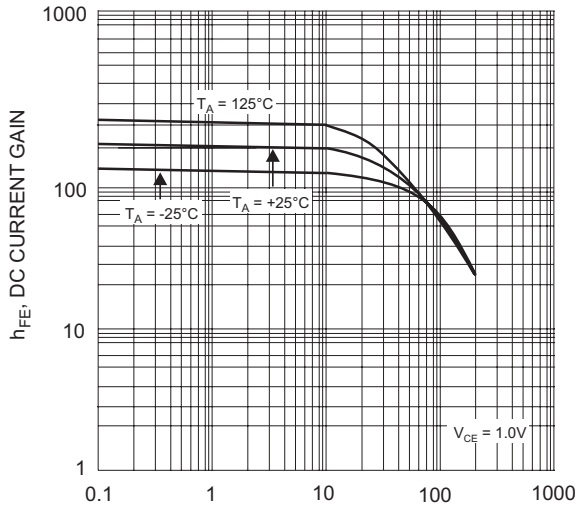
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



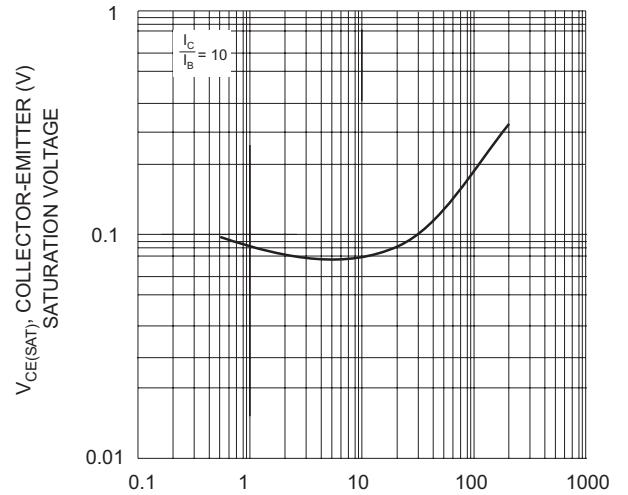
$T_A, \text{ AMBIENT TEMPERATURE (}^\circ\text{C)}$
Fig. 1, Max Power Dissipation vs Ambient Temperature



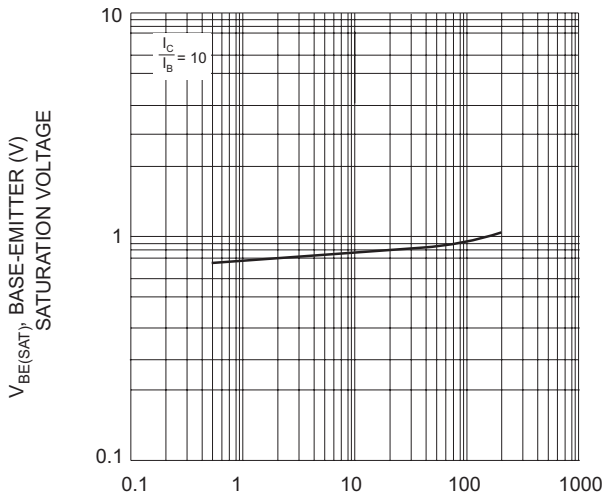
$V_{\text{CB}}, \text{ COLLECTOR-BASE VOLTAGE (V)}$
Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



$I_C, \text{ COLLECTOR CURRENT (mA)}$
Fig. 3, Typical DC Current Gain vs Collector Current



$I_C, \text{ COLLECTOR CURRENT (mA)}$
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



$I_C, \text{ COLLECTOR CURRENT (mA)}$
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current